

WHAT IS CLAIMED IS:

1. A method for producing a group III nitride compound semiconductor device, comprising steps of:

forming a first environment division and a second
5 environment division on a surface of a substrate; and
laminating a plurality of group III nitride compound semiconductor layers for constituting a device on said first environment division.

10 2. A producing method according to claim 1, wherein said first environment division is in a state in which said substrate surface is exposed. A

3. A producing method according to claim 2, wherein
15 said second environment division is made of a material which prevents said group III nitride compound semiconductors from being grown on said material.

20 4. A producing method according to claim 2, wherein a second group III nitride compound semiconductor layer, which is amorphous or different in crystallinity from said group III nitride compound semiconductor layers grown on said first environment division, is grown on said second environment division.

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5. A group III nitride compound semiconductor device comprising:

a substrate on which a first environment division and a

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second environment division are formed; and

group III nitride compound semiconductor layers formed on said first environment division so as to serve as effective semiconductor layers.

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6. A device according to claim 5, wherein said first environment division is in a state in which a surface of said substrate is exposed before said group III nitride compound semiconductor layers are formed.

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7. A device according to claim 6, wherein said second environment division is made of a material which prevents said group III nitride compound semiconductors from being grown on said material.

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8. A device according to claim 6, wherein a second group III nitride compound semiconductor layer, which is amorphous or different in crystallinity from said group III nitride compound semiconductor layers grown on said first environment division, is grown on said second environment division.

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